



IN THE SPECIFICATION

Please amend the paragraph beginning on page 6, line 18, as follows:

In still another embodiment of the present invention, a slurry may be used that has a higher mask 16 polish removal rate than the dielectric 19 +2 removal rate. This combines the functionality of the mask etch with the polish and may reduce or eliminate the mask etch part of the process shown in Figures 1 through 3.

Please amend the paragraph beginning on page 6, line 24, as follows:

In one embodiment, the polishing of the structure may only expose the top of the mask 16. This exposes the dielectric material 19 +2 to a reduced over-polishing relative to other techniques.